

21. (Twice Amended) A semiconductor device comprising:

- a gate member on a semiconductor;
- a source region in the semiconductor;
- a drain region in the semiconductor, said drain region having a depth shallower than said source region and not deeper than $0.1\text{ }\mu\text{m}$;
- a channel region being interposed between said source and drain regions and being adjacent to said gate [electrode] member, said channel region having a length not longer than $1\text{ }\mu\text{m}$, and

wherein said source and drain regions extends from a surface of said semiconductor to said depth not longer than a thickness of said semiconductor,

wherein said source region overlaps with said gate member while said drain region has an edge being coincide with that of said gate member.

36. (Twice Amended) A semiconductor device according to claim ~~33~~ 8 wherein said first silicon film is a floating gate which is formed over said first impurity region but [while said floating gate is] not formed over said second impurity region.

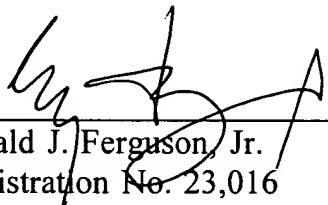
REMARKS

Reconsideration and allowance of this application are respectfully requested.

Referring to the rejection of claims 21-23 and 36 under 35 U.S.C. 112, second paragraph, claims 21 and 36 have been amended to avoid the informalities noted therein.

The allowance of claims 24-27, 33-35 and 37-44 is noted with appreciation.

Respectfully submitted,



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